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| SANYO | No. 1721A | 2SB1126/2SD1626 |
| | | PNP/NPN Epitaxial Planar Silicon Transistors For Various Drivers |

Applications

- . Relay drivers, hammer drivers, lamp drivers, motor drivers.

Features

- . High DC current gain (4000 or greater).
- . Large current capacity.
- . Very small size making it easy to provide high-density, small-sized hybrid IC's.

(): 2SB1126

Absolute Maximum Ratings at Ta=25°C

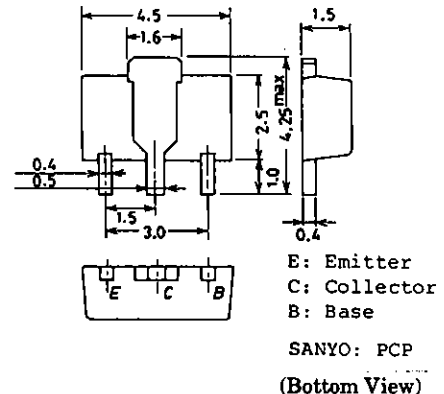
| | | | unit |
|------------------------------|---|-------------|------|
| Collector to Base Voltage | V_{CB0} | (-)80 | V |
| Collector to Emitter Voltage | V_{CEO} | (-)50 | V |
| Emitter to Base Voltage | V_{EBO} | (-)10 | V |
| Collector Current | I_C | (-)1.5 | A |
| Collector Current(Pulse) | I_{CP} | (-)3 | A |
| Collector Dissipation | P_C | 500 | mW |
| | Mounted on ceramic board (250mm ² x 0.8mm) | 1.5 | W |
| Junction Temperature | T_j | 150 | °C |
| Storage Temperature | T_{stg} | -55 to +150 | °C |

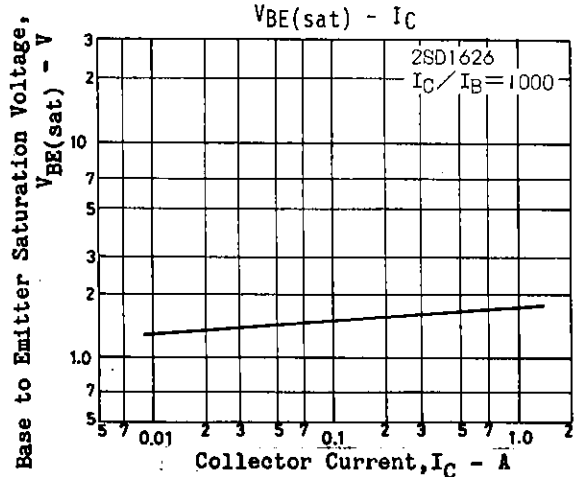
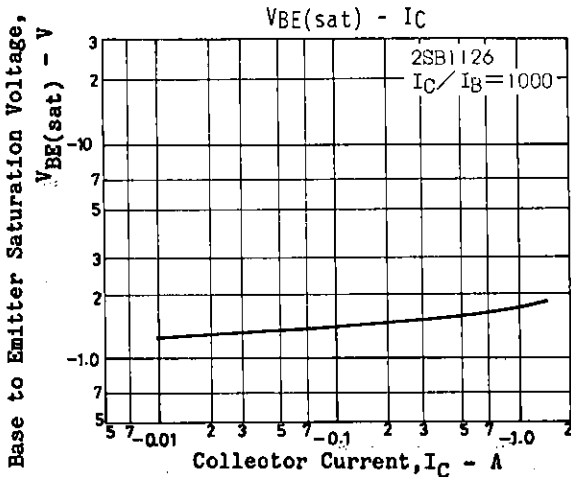
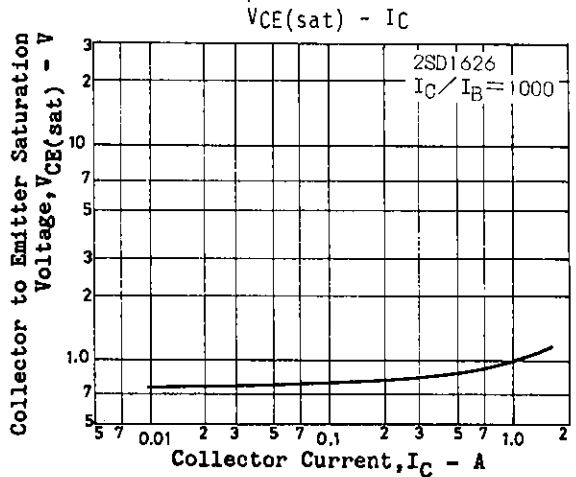
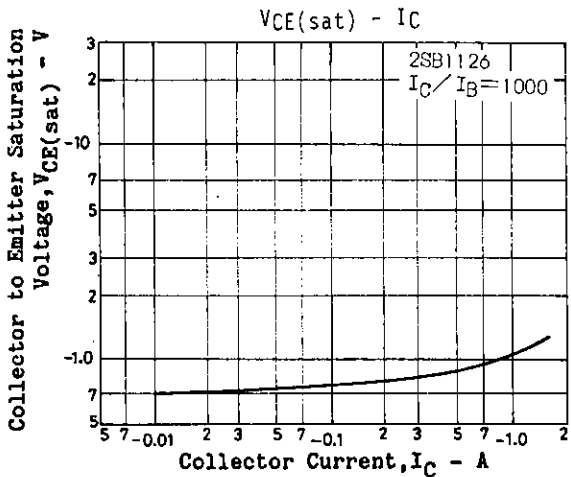
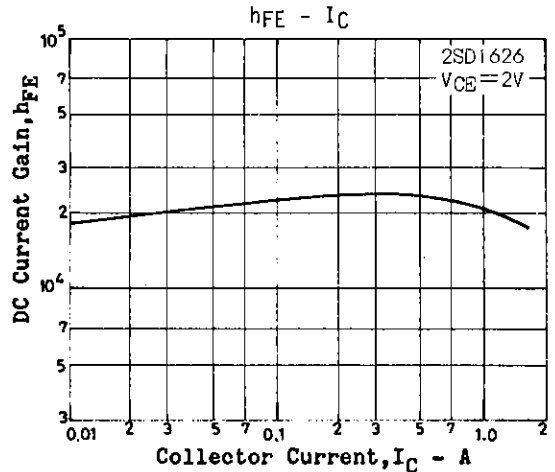
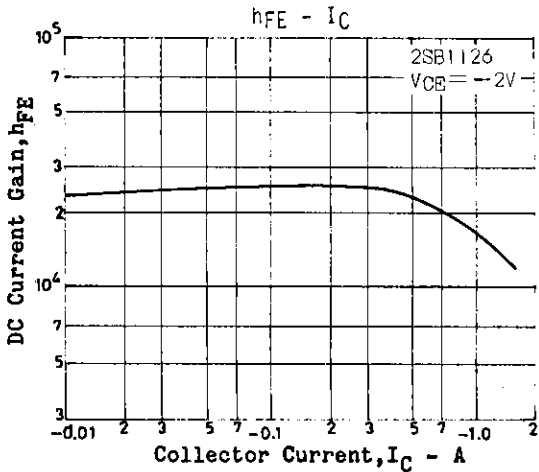
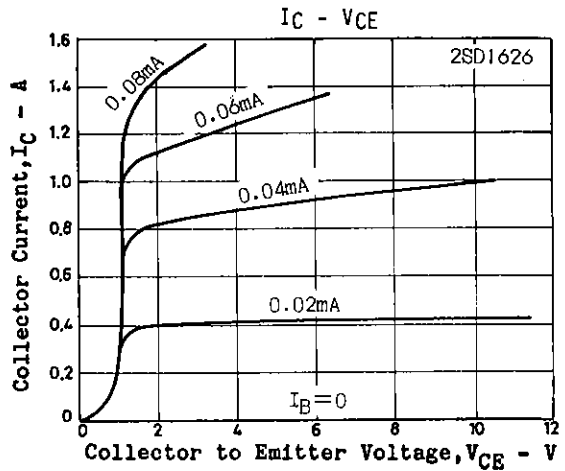
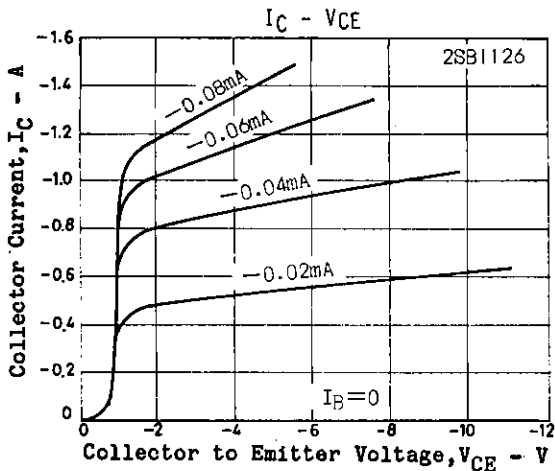
Electrical Characteristics at Ta=25°C

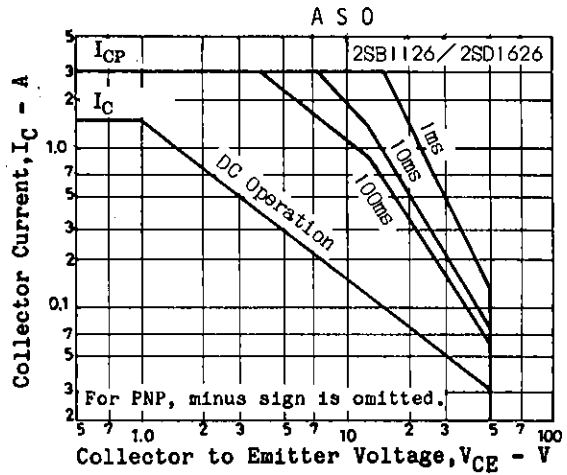
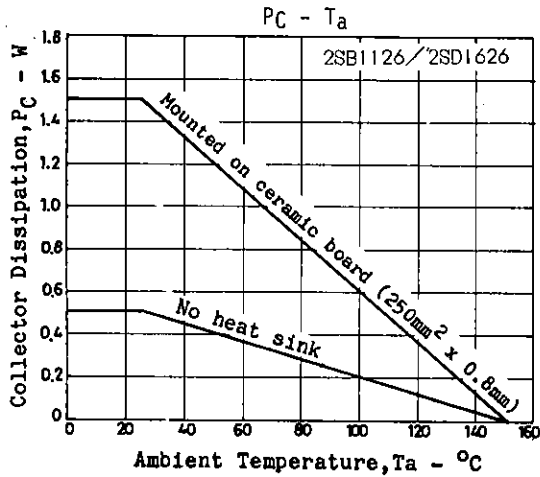
| | | | min | typ | max | unit |
|--------------------------|---------------|------------------------------|--------|--------|--------|------|
| Collector Cutoff Current | I_{CBO} | $V_{CB}=(-)40V, I_E=0$ | | | (-)100 | nA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB}=(-)8V, I_C=0$ | | | (-)100 | nA |
| DC Current Gain | h_{FE1} | $V_{CE}=(-)2V, I_C=(-)500mA$ | 4000 | | | |
| | h_{FE2} | $V_{CE}=(-)2V, I_C=(-)10mA$ | 3000 | | | |
| Gain-Bandwidth Product | f_T | $V_{CE}=(-)10V, I_C=(-)50mA$ | | 120 | | MHz |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C=(-)500mA, I_B=(-)0.5mA$ | (-)0.9 | (-)1.5 | | V |
| B-E Saturation Voltage | $V_{BE(sat)}$ | $I_C=(-)500mA, I_B=(-)0.5mA$ | (-)1.5 | (-)2.0 | | V |
| C-B Breakdown Voltage | $V_{(BR)CBO}$ | $I_C=(-)10\mu A, I_E=0$ | (-)80 | | | V |
| C-E Breakdown Voltage | $V_{(BR)CEO}$ | $I_C=(-)1mA, R_{BE}=\infty$ | (-)50 | | | V |
| E-B Breakdown Voltage | $V_{(BR)EBO}$ | $I_E=(-)10\mu A, I_C=0$ | (-)10 | | | V |

Marking 2SB1126:BI
2SD1626:DI

Package Dimensions 2038
(unit:mm)







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